PC355NT

Opaque*, **Mini-Flat** Package,
High Sensitivity **Photocoupler**

■ Features

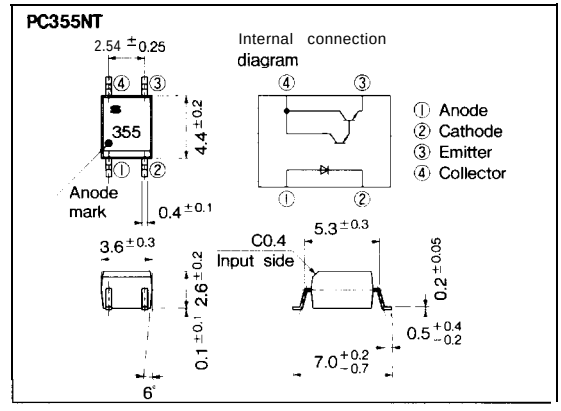
1. High current transfer ratio
   (CTR : MIN. 600% at I_F = lmA, V_{CE} = 2V)
2. Opaque type, mini-flat package
   PC355NT (l-channel)
3. Subminirature type
   (The volume is smaller than that of our conventional DIP type by as far as 30%)
4. Isolation voltage between input and output
   PC355NT·· ·Viso : 3 750V_{rms}

* Employs double transfer mold technology

■ Applications

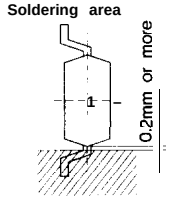
1. Hybrid substrates that require high density mounting.
2. Programmable controllers

■ Outline Dimensions (Unit : mm)



■ Absolute Maximum Ratings (Ta=25℃)

Parameter		Symbol	Rating	Unit
Input	Forward current	I_F	50	mA
	*1 Peak forward current	I_{FM}	1	A
	Reverse voltage	V_R	6	v
	Power dissipation	P	70	mW
output	Collector -emitter voltage	V_{CEO}	35	v
	Emitter -collector voltage	V_{ECO}	6	v
	Collector current	I_C	80	mA
	Collector power dissipation	P_C	150	mW
Total power dissipation		P_{tot}	170	mW
*2 Isolation voltage		V_{iso}	3 750	V_{rms}
Operating temperature		T_{opr}	−30 to +100	℃
Storage temperature		T_{stg}	−40 to +125	℃
*3 Soldering temperature		T_{sol}	260	℃



*1 Pulse width ≦ 100 μs, Duty ratio = 0.001
*2 40 to 60%RH, AC for 1 minute
*3 For 10 senconds

■ Electro-optical Characteristics (Ta=25℃)

Parameter			Symbol	Conditions	MIN.	TYP.		
Input	Forward voltage		V_F	I_F = 20mA	−	1.2	1.4	V
	Reverse current		I_R	V_R = 4V	−	−	10	μA
	Terminal capacitance		C_t	V=0, f=1kHz	−	30	250	pF
output	Collector dark current		I_{CEO}	V_{CE} = 10V, I_F = 0	−	−	10^{-6}	A
	Collector emitter breakdown voltage		BV_{CEO}	I_C = 0.1mA, I_F = 0	35		−	V
	Emitter -collector breakdown voltage		BV_{ECO}	I_E = 10 μA, I_F = 0	6		−	V
Transfer characteristics	Current transfer ratio		CTR	I_F = 1mA, V_{CE} = 2V	600	1 600	7500	%
	Collector-emitter saturation voltage		$V_{CE(sat)}$	I_F = 20mA, I_C = 1mA	−	0.8	1.0	V
	Isolation resistance		R_{ISO}	DC500V, 40 to 60%RH	5×10^{10}	10^{11}		Ω
	Floating capacitance		C_f	V=O, f=1MHz	−	0.6	1.0	pF
	Response time	Rise time	t_r	V_{CE} = 2V, I_C = 2mA	−	60	300	μs
		Fall time	t_f	R_L = 100Ω	−	53	250	μs

Fig. 1 Forward Current vs. Ambient Temperature

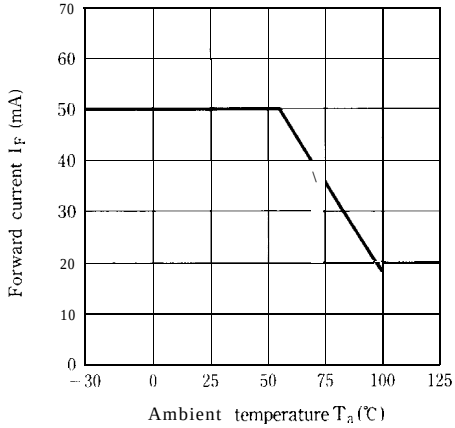


Fig. 2 Diode Power Dissipation vs. Ambient Temperature

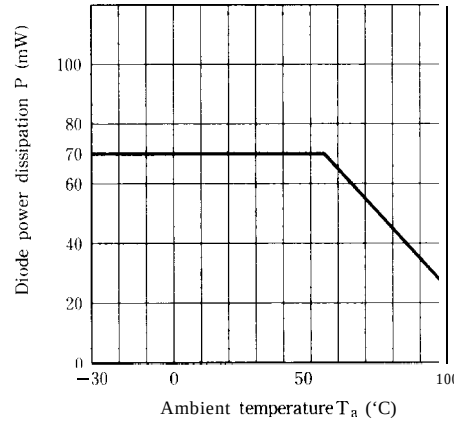


Fig. 3 Collector Power Dissipation vs. Ambient Temperature

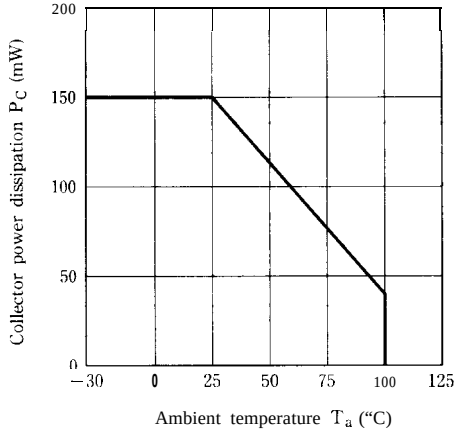


Fig. 4 Total Power Dissipation vs. Ambient Temperature

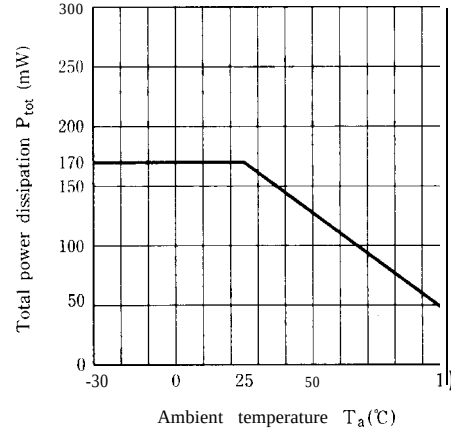


Fig. 5 Peak **Forward Current** vs. **Duty Ratio**

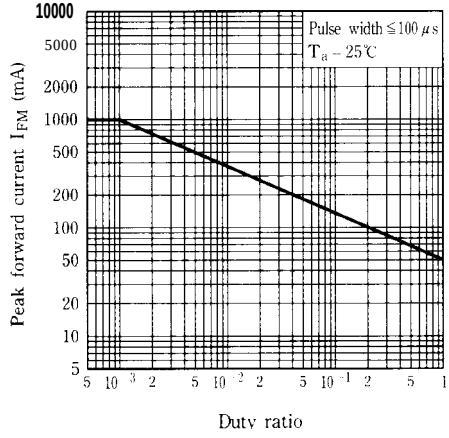


Fig. 6 Forward Currant vs. Forward Voltage

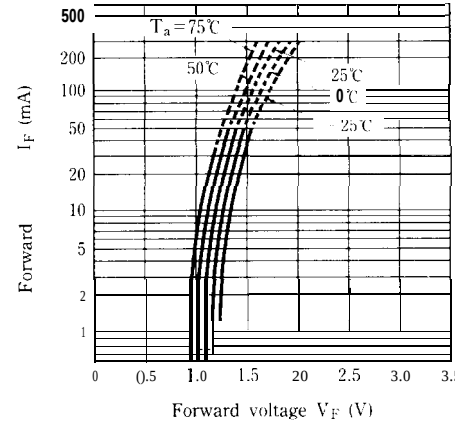


Fig. 7 Current Transfer Ratio vs. Forward Current

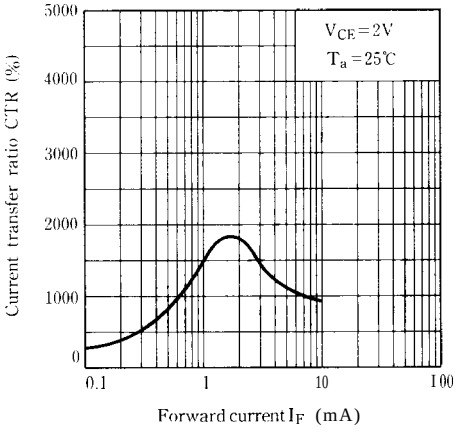


Fig. 8 Collector Current vs. Collector-emitter Voltage

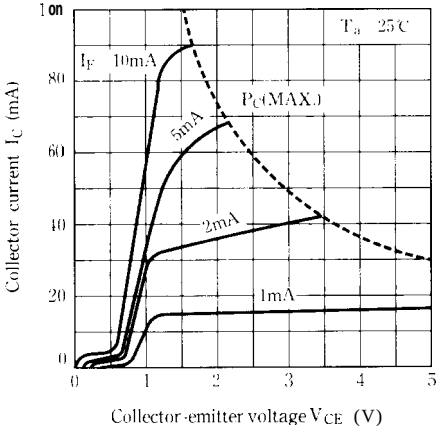


Fig. 9 Relative Current Transfer Ratio vs. Ambient Temperature

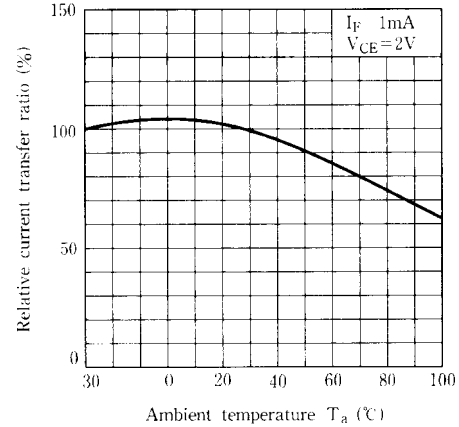


Fig.10 Collector-emitter Saturation voltage vs. Ambient Temperature

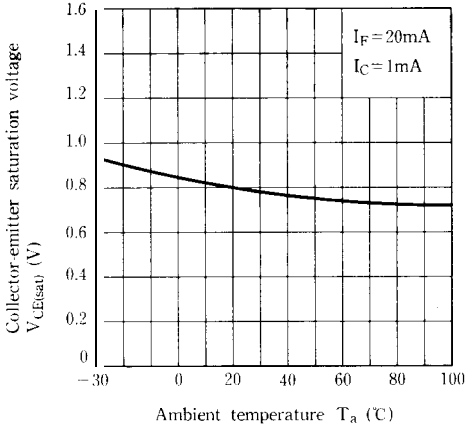


Fig.11 Collector Dark Current vs. Ambient Temperature

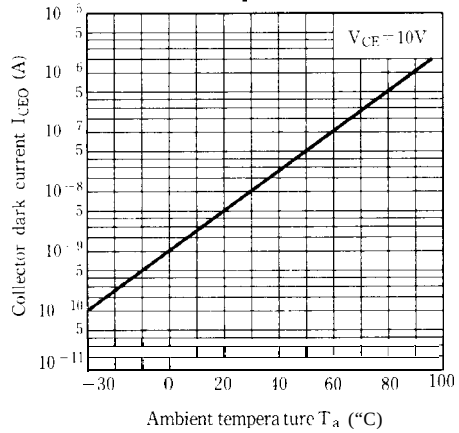
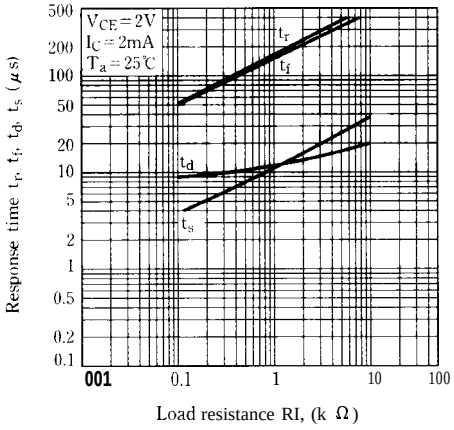


Fig.12 Responce Time vs. Load Resistance



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Photocouplers

Test Circuit For Response Time

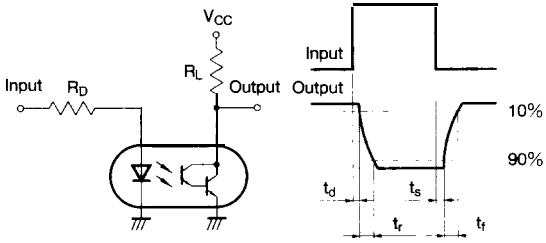
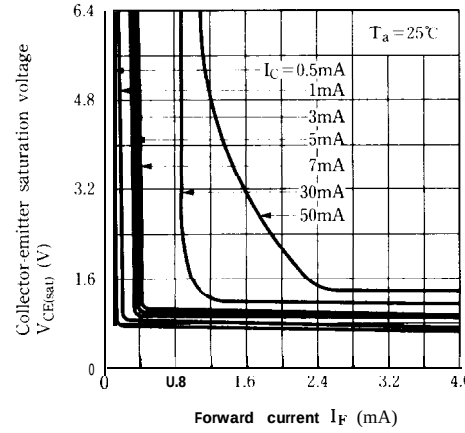


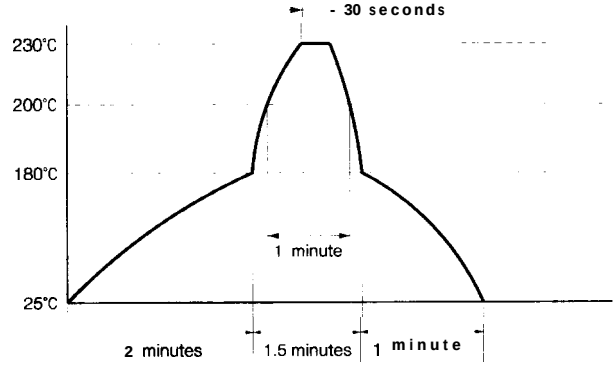
Fig.13 Collector-emitter Saturation Voltage vs. Forward Current



■ Temperature Profile of Soldering Reflow

(1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.

PC355NT



(2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device.

Keep the temperature on the package of the device within the condition of above (l).

. Please refer to the chapter “Precautions for Use.” (Page 78 to 93)